



제 29회 한국반도체학술대회

The 29th Korean Conference on Semiconductors

2022년 1월 24일(월)~ 26일(수) | 강원도 하이원 그랜드호텔(컨벤션타워)

2022년 1월 25일(화), 16:00-17:45

Room C (사파이어 I, 5층)

K. Memory (Design & Process Technology) 분과

[TC3-K] Ferroelectric Memory

좌장: 배종호 교수(국민대학교), 이선우 교수(인하공업전문대학)

<p>TC3-K-1 16:00-16:15</p>	<p>Tuning Operating Range of Organic Field Effect Transistors through Control of Gate Dielectric Layer Thickness Yongju Lee^{1,2}, Hyo Won Jang¹, Boram Kim¹, Swarup Biswas¹, Yoon Kim¹, and Hyeok Kim¹ <i>¹School of Electrical and Computer Engineering, CS4, University of Seoul, ²Applied Robot R&D Department, KITECH</i></p>
<p>TC3-K-2 16:15-16:30</p>	<p>Investigation of Tungsten Electrode Effect on Ferroelectricity of ALD-Hf_{0.5}Zr_{0.5}O₂ Thin Films Jeong Gyu Yoo¹, Jaidah Mohan², Yong Chan Jung², Namhun Kim^{2,3}, Hyo Jeong Kim¹, Hye Ryeon Park¹, Min Kwan Cho¹, Heber Hernandez-Arriaga², Harrison Sejoon Kim², Rino Choi³, Jiyoung Kim², and Si Joon Kim¹ <i>¹Kangwon National University, ²The University of Texas at Dallas, ³Inha University</i></p>
<p>TC3-K-3 16:30-16:45</p>	<p>전기장 사이클링을 통한 Hf_xZr_{1-x}O₂박막의 상전이영역으로의 결정화 유도 Kim, S.¹, Moon, S. G.², Park, W. Y.², Im, K.¹, and Cho, B. J.¹ <i>¹KAIST, ²SK Hynix</i></p>
<p>TC3-K-4 16:45-17:00</p>	<p>Effect of Oxygen Content in IGZO Channels on Ferroelectric Memory Properties Hyojin Yang, Sung-jin Choi, Dong Myong Kim, Daewoong Kwon, Dae Hwan Kim, and Jong-Ho Bae <i>School of Electrical Engineering, Kookmin University</i></p>
<p>TC3-K-5 17:00-17:15</p>	<p>Large Memory-Window (>5V), Multi-Bit Operation (8 states), High Speed (<20ns) and High Endurance (10⁹) Ferroelectric FET and High CDE/CFE Stack for 3D Ferroelectric NAND Flash Memory Giuk Kim, Sangho Lee, Taehyong Eom, and Sanghun Jeon <i>School of Electrical Engineering, KAIST</i></p>
<p>TC3-K-6 17:15-17:30</p>	<p>Strategies for High-Performance and High-Endurance HfO₂-Based Ferroelectric Field Effect Transistor Memory Taeho Kim, Junghyeon Hwang, Giuk Kim, Minhyun Jung, and Sanghun Jeon <i>School of Electrical Engineering, KAIST</i></p>
<p>TC3-K-7 17:30-17:45</p>	<p>Investigation of Ferroelectric Properties of Hf_{0.5}Zr_{0.5}O₂ Thin Films according to Annealing Conditions Hye Ryeon Park¹, Hyo Jeong Kim¹, Yong Chan Jung², Jaidah Mohan², Sung Min Rho³, Min Seong Kim³, Jeong Gyu Yoo¹, Min Kwan Cho¹, Heber Hernandez-Arriaga², Jin-Hyun Kim², Harrison Sejoon Kim², Hyun Jae Kim³, Jiyoung Kim², and Si Joon Kim¹ <i>¹Kangwon National University, ²The University of Texas at Dallas, ³Yonsei University</i></p>